



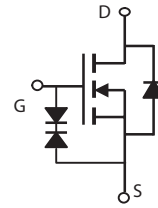
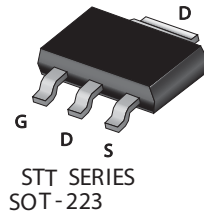
N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
90V	1.4A	600 @ V _{GS} =10V
		708 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	90	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^{a e}	T _A =25°C	1.4
		T _A =70°C	1.12
I _{DM}	-Pulsed ^b	9.3	A
E _{AS}	Single Pulse Avalanche Energy ^d	0.49	mJ
P _D	Maximum Power Dissipation ^a	T _A =25°C	3
		T _A =70°C	1.9
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	42	°C/W
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ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	90			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =72V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.7	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =0.7A		480	600	m ohm
		V _{GS} =4.5V , I _D =0.65A		525	708	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =0.7A		2.5		S
DYNAMIC CHARACTERISTICS ^c						
C _{iss}	Input Capacitance	V _{DS} =25V,V _{GS} =0V f=1.0MHz		170		pF
C _{oss}	Output Capacitance			22		pF
C _{rSS}	Reverse Transfer Capacitance			13		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =45V I _D =0.7A V _{GS} =10V R _{GEN} = 6 ohm		14.5		ns
t _r	Rise Time			11.5		ns
t _{D(OFF)}	Turn-Off Delay Time			172		ns
t _f	Fall Time			26		ns
Q _g	Total Gate Charge	V _{DS} =45V,I _D =0.7A,V _{GS} =10V		3.2		nC
		V _{DS} =45V,I _D =0.7A,V _{GS} =4.5V		1.8		nC
Q _{gs}	Gate-Source Charge	V _{DS} =45V,I _D =0.7A, V _{GS} =10V		0.65		nC
Q _{gd}	Gate-Drain Charge			0.9		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =0.7A		0.87	1.3	V

Notes

- a.Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.
b.Pulse Test:Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
c.Guaranteed by design, not subject to production testing.
d.Starting $T_J=25^{\circ}\text{C}$, $L=0.5\text{mH}$, $V_{DD}=40V$.(See Figure13)
e.Drain current limited by maximum junction temperature.

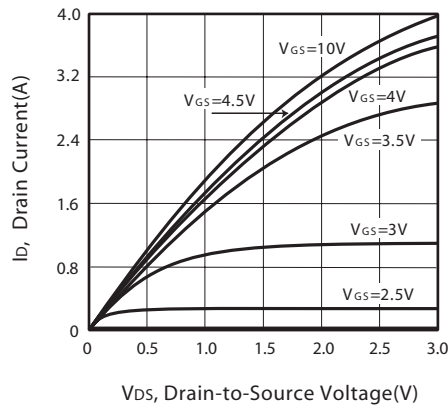


Figure 1. Output Characteristics

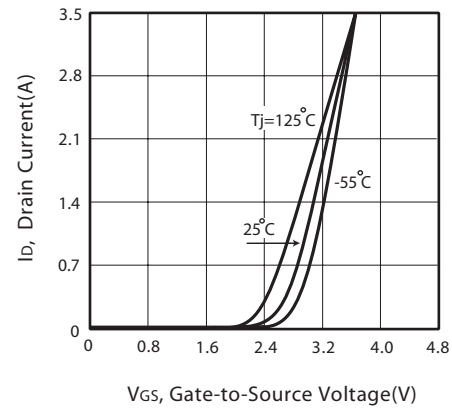


Figure 2. Transfer Characteristics

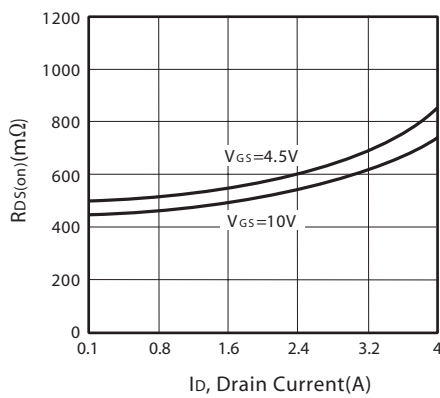


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

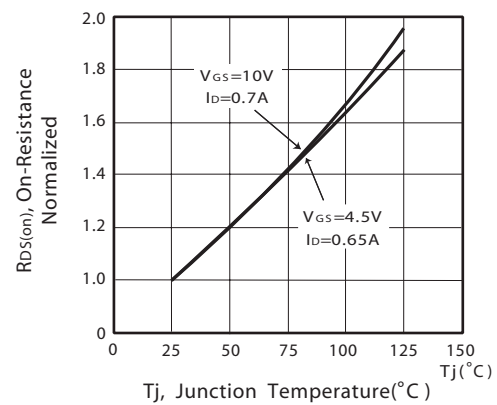


Figure 4. On-Resistance Variation with Drain Current and Temperature

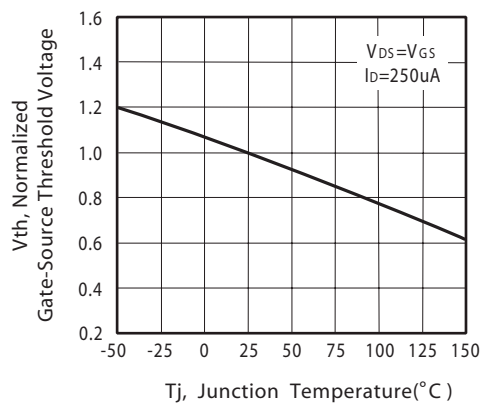


Figure 5. Gate Threshold Variation with Temperature

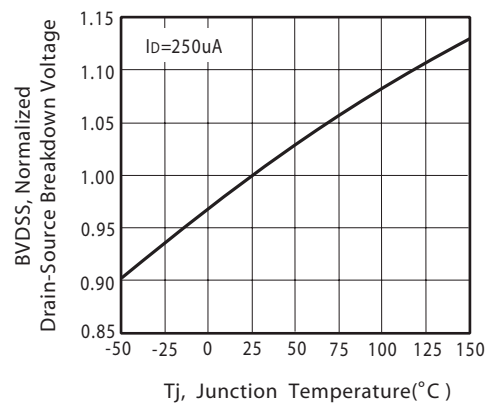


Figure 6. Breakdown Voltage Variation with Temperature

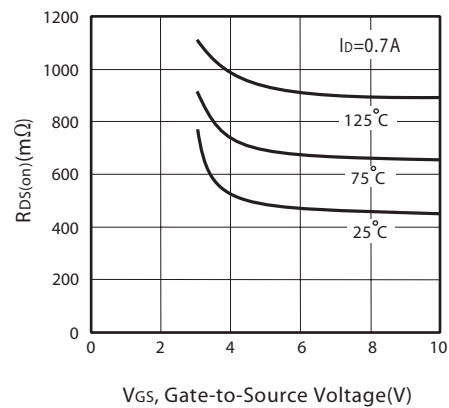


Figure 7. On-Resistance vs. Gate-Source Voltage

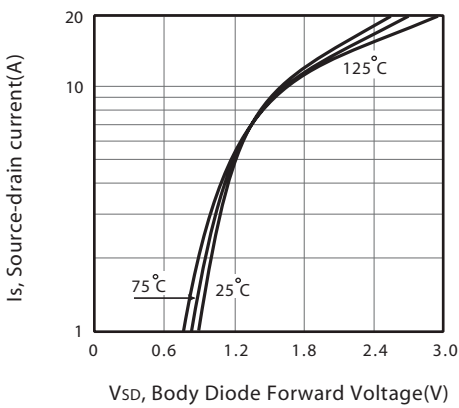


Figure 8. Body Diode Forward Voltage Variation with Source Current

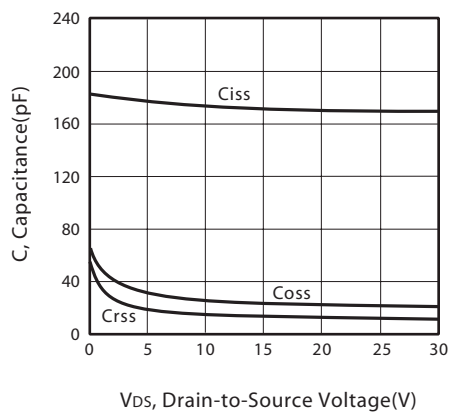


Figure 9. Capacitance

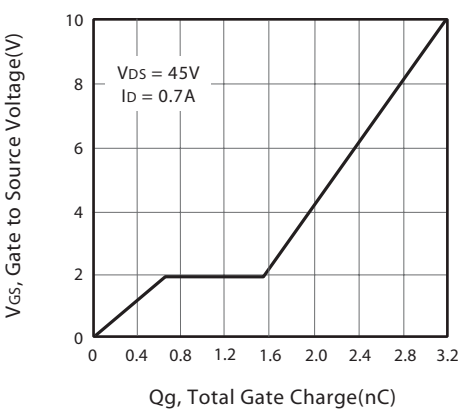


Figure 10. Gate Charge

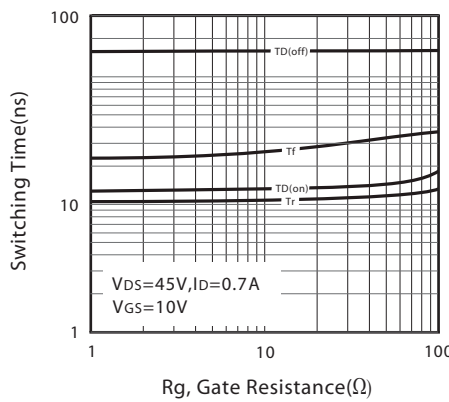


Figure 11. switching characteristics

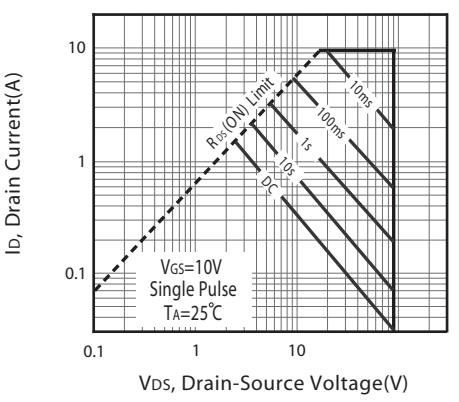
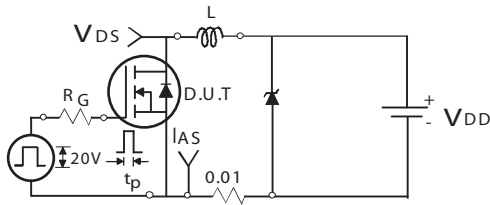
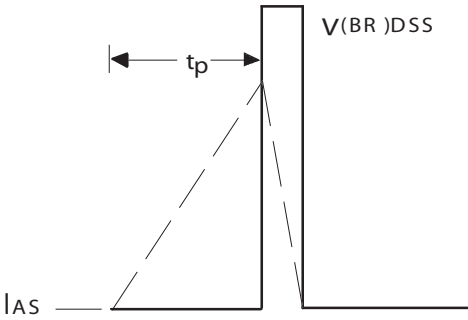


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

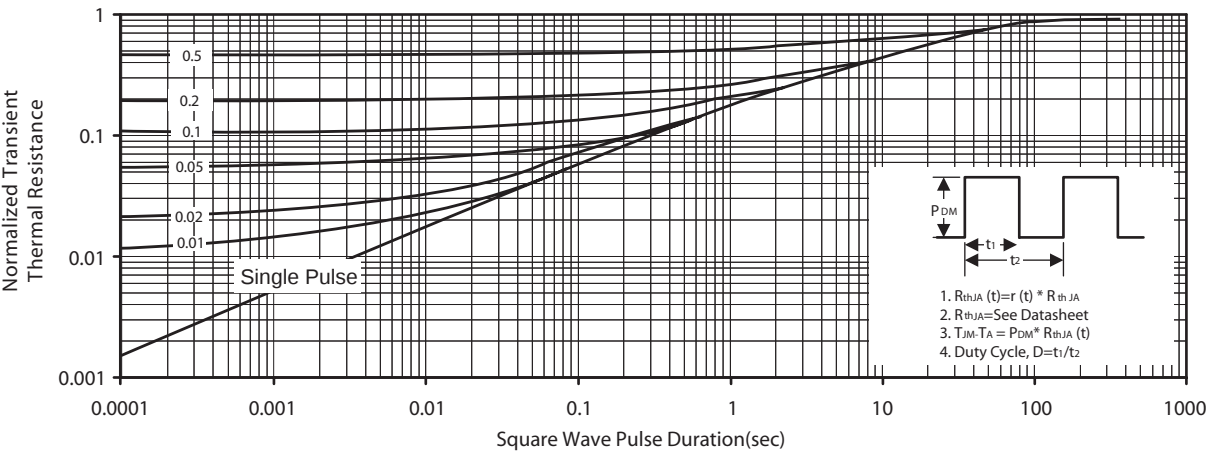
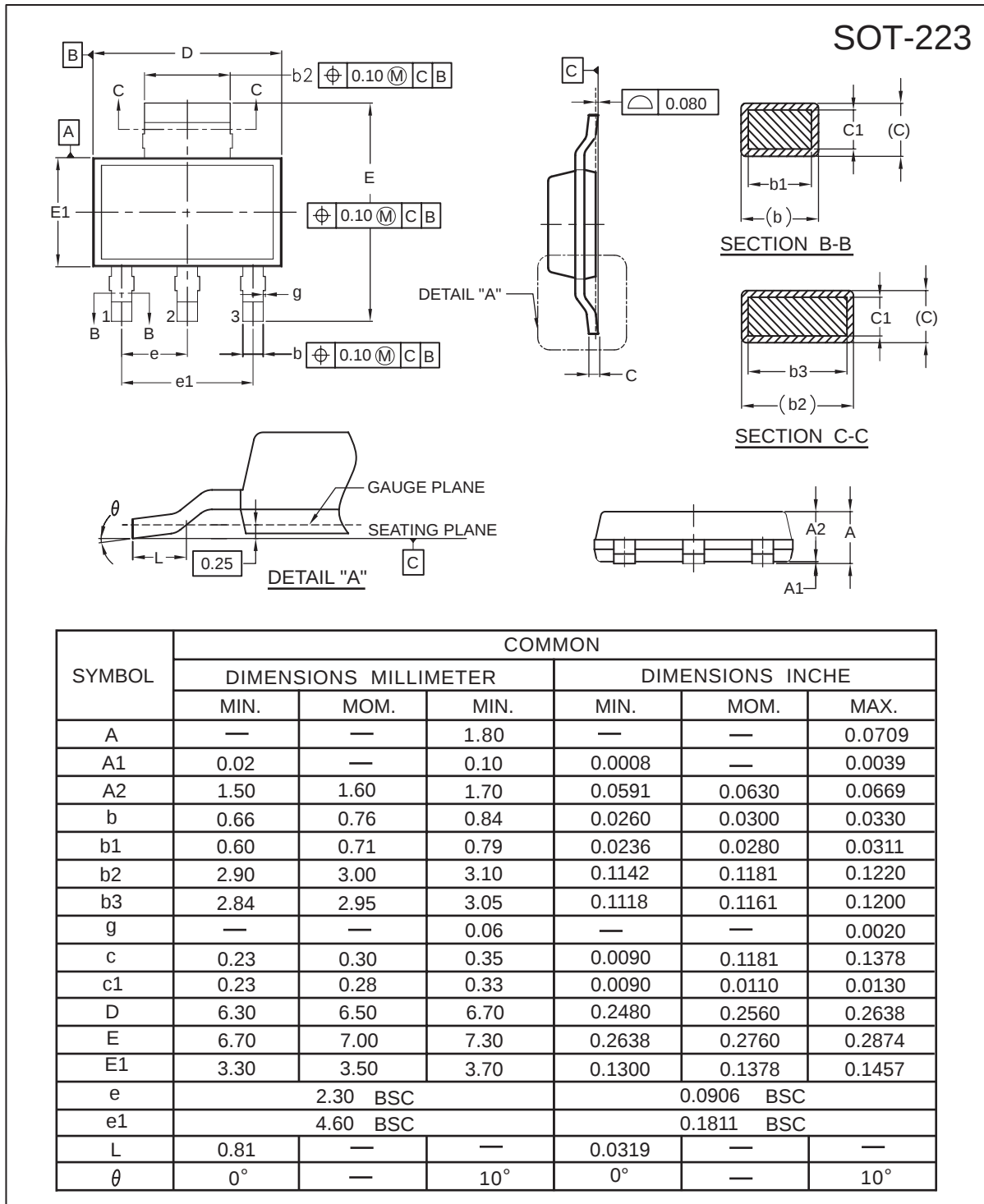
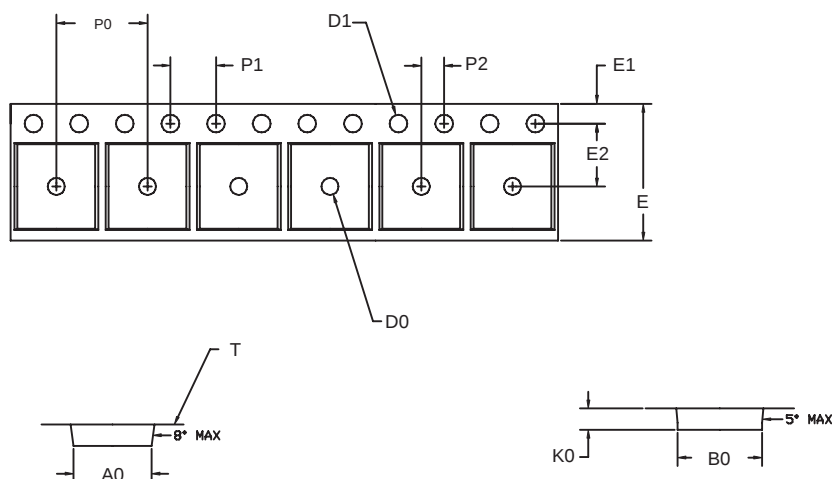


Figure 14. Normalized Thermal Transient Impedance Curve



SOT-223 Tape and Reel Data

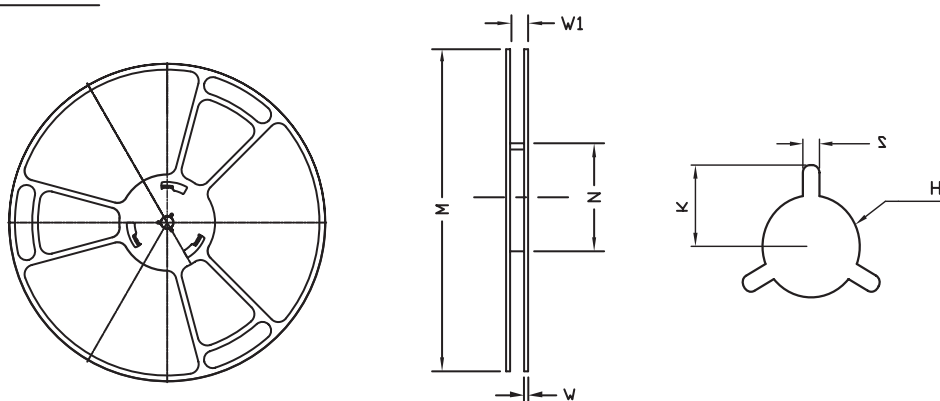
SOT-223 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
---	6.83 ±0.1	7.42 ±0.1	1.88 ±0.1	1.50 +0.25	1.60 +0.1	12.0 +0.3 -0.1	1.75 ±0.1	5.50 ±0.5	8.0 ±0.1	4.00 ±0.1	2.00 ±0.05	0.292 ±0.02

SOT-223 Reel



UNIT:mm

REEL SIZE	M	N	W	W1	H	K	S	G	R	V
φ 330 ± 0.5	---	φ 97.0 ± 1.0	2.2	13.0 + 1.5	φ 13.0 + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---